

Yang Lv

List of Publications by Year in descending order

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docs citations

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1565
citing authors

#	ARTICLE	IF	CITATIONS
1	Ferromagnetic resonance and magnetization switching characteristics of perpendicular magnetic tunnel junctions with synthetic antiferromagnetic free layers. Applied Physics Letters, 2022, 120, .	3.3	7
2	Bipolar Electric-Field Switching of Perpendicular Magnetic Tunnel Junctions through Voltage-Controlled Exchange Coupling. Nano Letters, 2022, 22, 622-629.	9.1	15
3	Bipolar Random Spike and Bipolar Random Number Generation by Two Magnetic Tunnel Junctions. IEEE Transactions on Electron Devices, 2022, 69, 1582-1587.	3.0	5
4	Large unidirectional spin Hall and Rashba-Edelstein magnetoresistance in topological insulator/magnetic insulator heterostructures. Applied Physics Reviews, 2022, 9, .	11.3	13
5	Sub-ns Switching and Cryogenic-Temperature Performance of Mo-Based Perpendicular Magnetic Tunnel Junctions. IEEE Electron Device Letters, 2022, 43, 1215-1218.	3.9	3
6	Ultralow Current Switching of Synthetic-Antiferromagnetic Magnetic Tunnel Junctions Via Electric-Field Assisted by Spin-Orbit Torque. Advanced Electronic Materials, 2022, 8, .	5.1	3
7	Influence of size and shape on key performance metrics in spin-torque oscillators. AIP Advances, 2021, 11, .	1.3	1
8	Experimental Demonstration of Probabilistic Spin Logic by Magnetic Tunnel Junctions. IEEE Magnetics Letters, 2019, 10, 1-5.	1.1	19
9	Independent Control of Antiparallel- and Parallel-State Thermal Stability Factors in Magnetic Tunnel Junctions for Telegraphic Signals With Two Degrees of Tunability. IEEE Transactions on Electron Devices, 2019, 66, 5353-5359.	3.0	11
10	$\frac{L}{L_0} > 1$ Synthetic Antiferromagnet through an fcc Ru Spacer Utilized for Perpendicular Magnetic Tunnel Junctions. Physical Review Applied, 2018, 9, .	3.8	23
11	Enhancement of tunneling magnetoresistance by inserting a diffusion barrier in L1-FePd perpendicular magnetic tunnel junctions. Applied Physics Letters, 2018, 112, .	3.3	15
12	Unidirectional spin-Hall and Rashba-Edelstein magnetoresistance in topological insulator-ferromagnet layer heterostructures. Nature Communications, 2018, 9, 111.	12.8	87
13	Efficient In-Memory Processing Using Spintronics. IEEE Computer Architecture Letters, 2018, 17, 42-46.	1.5	49
14	Telegraphic switching signals by magnet tunnel junctions for neural spiking signals with high information capacity. Journal of Applied Physics, 2018, 124, .	2.5	24
15	Demonstration of Ru as the 4th ferromagnetic element at room temperature. Nature Communications, 2018, 9, 2058.	12.8	29
16	Room-temperature high spin-orbit torque due to quantum confinement in sputtered BixSe(1-x) films. Nature Materials, 2018, 17, 800-807.	27.5	344
17	Effect of capping layer on formation and magnetic properties of MnBi thin films. Journal of Applied Physics, 2017, 122, 213904.	2.5	6
18	Spin Analog-to-Digital Converter Using Magnetic Tunnel Junction and Spin Hall Effect. IEEE Electron Device Letters, 2015, 36, 511-513.	3.9	23

#	ARTICLE	IF	CITATIONS
19	Giant Spin Pumping and Inverse Spin Hall Effect in the Presence of Surface and Bulk Spin-Orbit Coupling of Topological Insulator Bi ₂ Se ₃ . Nano Letters, 2015, 15, 7126-7132.	9.1	257
20	Sputtering of cobalt film with perpendicular magnetic anisotropy on disorder-free graphene. AIP Advances, 2014, 4, .	1.3	9
21	The effect of electric field induced magnetic anisotropy in ferromagnetic resonance in magnetic tunnel junctions. , 2014, , .		0